



Docket No.: M4065.0051/P051-A
(PATENT)

#16/AMDT
D
4/12/02
VJ

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Leonard Forbes, et al.

Application No.: 09/609,813

Group Art Unit: 2815

Filed: July 3, 2000

Examiner: P. Brock

For: HIGH DENSITY PLANAR SRAM CELL
USING BIPOLAR LATCHUP AND GATED
DIODE BREAKDOWN

RECEIVED
APR 10 2002
TECHNOLOGY CENTER 2800

AMENDMENT

Box Non-Fee Amendment

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated January 9, 2002 (Paper No. 15), please amend the above-identified U.S. patent application as follows:

In the Claims

Please add new claim 62 as follows:

sub G3
D' A method of forming a circuit for storing information as one of at least two possible stable current states, the method comprising:

providing a semiconductor substrate; providing doped silicon regions to form a multi-region planar thyristor having at least four regions;

forming at least one polysilicon gate overlying a single junction of said multi-region planar thyristor thereby making said single junction a gated diode; and